

## Amendments to the Claims

82 7. (amended) A process for forming an electrical connection to a semiconductor device comprising:

forming a first metal-containing layer, wherein the first metal containing layer:

contacts an exposed region that includes silicon carbide; and

has a composition that does not form an ohmic contact with a doped silicon carbide if annealed for a time period of less than ten hours and at a temperature less than a melting point of a material within the metal-containing layer; and

annealing the metal-containing layer and the exposed region at a temperature less than the melting point of the metal-containing layer and for a period of time in excess of ten hours, wherein a substantially continuous ohmic contact region is formed between the first metal-containing layer and the silicon carbide.

8. (original) The process of claim 7, wherein the material is aluminum.

9. (original) The process of claim 7, wherein annealing is performed for a time period of at least twenty hours at a temperature in a range of approximately 400-660 C

10. (original) The process of claim 7, wherein the composition is substantially pure aluminum.

11. (original) The process of claim 7, wherein: the claim 7, wherein: the material is aluminum; and the composition comprises aluminum and a first dopant, wherein the composition is at least approximately 90 weight percent aluminum.

12. (original) The process of claim 7, wherein annealing is performed for a time period of at least approximately 25 hours.

13. (original)            The process of claim 7, wherein annealing is performed at a temperature no greater than approximately 660 degrees.
14. (original)            The process of claim 7, wherein annealing forms an aluminum silicon carbide alloy.
15. (original)            The process of claim 7, wherein the exposed region is p-type doped.
16. (original)            The process of claim 7, wherein annealing is performed in a vacuum.
17. (original)            The process of claim 7, wherein annealing is performed using a noble gas.
18. (original)            The process of claim 7, further comprising:  
                              removing a portion of the first metal containing layer; and  
                              forming second metal containing layer over the contact region.
19. (original)            A process for forming an electrical connection to a semiconductor device comprising:  
                              forming a metal-containing layer that contacts an exposed region, wherein the exposed region includes silicon carbide; and  
                              annealing the metal-containing layer and substrate for a time period of at least approximately ten hours and at a temperature of at least approximately 300 C.
20. (original)            The process of claim 19, wherein the metal-containing layer is substantially pure aluminum.
21. (original)            The process of claim 19, wherein the metal-containing layer comprises at least approximately 90 weight percent aluminum.

22. (original) The process of claim 19, wherein annealing is performed for a time period of at least approximately 25 hours.

23. (original) The process of claim 19, wherein annealing is performed at a temperature no greater than approximately 660 degrees. 24. The process of claim 19, wherein annealing forms an aluminum silicon carbide alloy.

25. (original) The process of claim 19, wherein the exposed region is ptype doped.

26. (original) The process of claim 19, wherein annealing is performed in a vacuum.

27. (original) The process of claim 19, wherein annealing is performed using a noble gas.

28. (original) The process of claim 19, wherein annealing forms an ohmic contact between the metal-containing layer and the exposed region.